



General Description

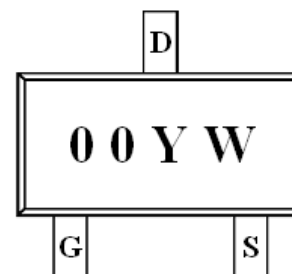
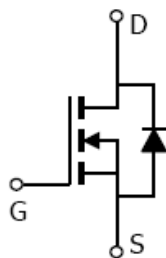
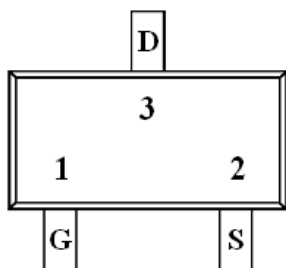
AFN3400, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- 30V/4.0A, $R_{DS(ON)}=48m\Omega@V_{GS}=10V$
- 30V/3.5A, $R_{DS(ON)}=52m\Omega@V_{GS}=4.5V$
- 30V/2.8A, $R_{DS(ON)}=58m\Omega@V_{GS}=2.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- SOT-23-3L package design

Pin Description (SOT-23-3L)



Application

- Power Management in Note book
- LED Display
- DC-DC System
- LCD Panel

Pin Define

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN3400S23RG	00YW	SOT-23-3L	Tape & Reel	3000 EA

- ※ 00 parts code
- ※ Y year code (0 ~ 9)
- ※ W week code (A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52)
- ※ AFN3400S23RG : 7" Tape & Reel ; Pb- Free ; Halogen- Free



Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	30	V
Gate –Source Voltage	V _{GSS}	±12	V
Continuous Drain Current(T _J =150°C)	I _D	T _A =25°C	4.0
		T _A =70°C	3.5
Pulsed Drain Current	I _{DM}	20	A
Continuous Source Current(Diode Conduction)	I _S	1.5	A
Power Dissipation	P _D	T _A =25°C	1.25
		T _A =70°C	0.8
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	120	°C/W

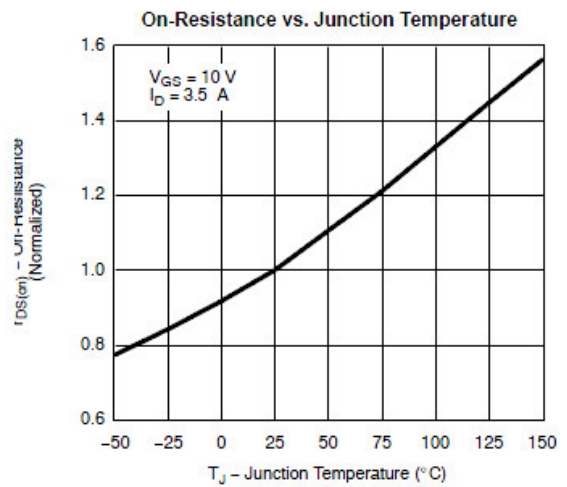
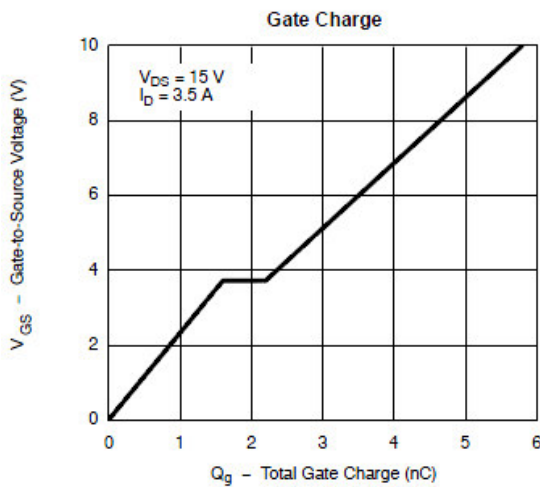
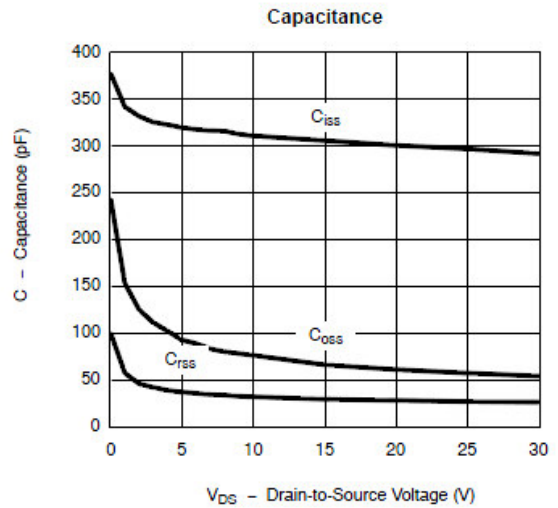
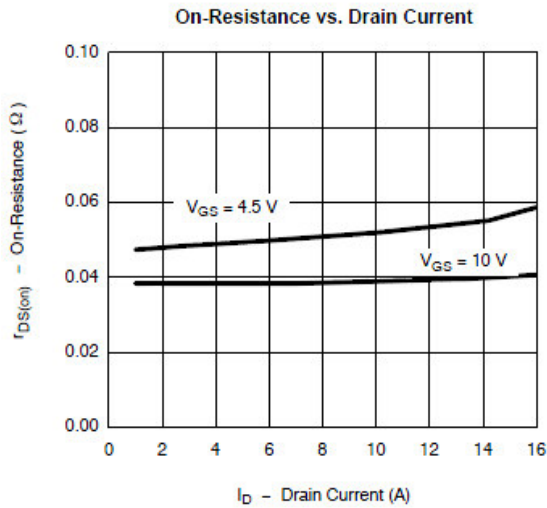
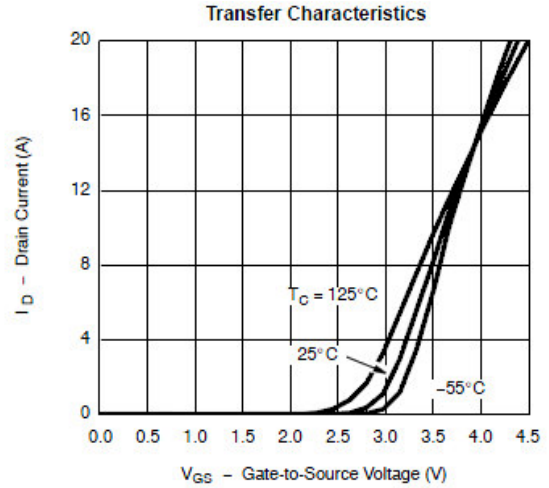
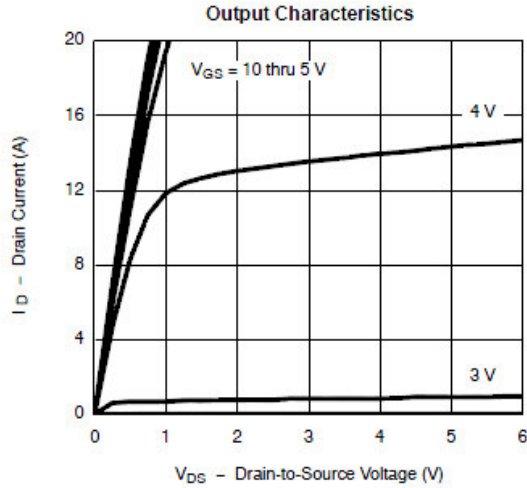
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250uA	30			V	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	0.4		1.0	V	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =24V, V _{GS} =0V			1	uA	
		V _{DS} =24V, V _{GS} =0V T _J =85°C			30		
On-State Drain Current	I _{D(on)}	V _{DS} ≥ 4.5V, V _{GS} =10V	6			A	
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =4.0A		40	48	mΩ	
		V _{GS} =4.5V, I _D =3.5A		44	52		
		V _{GS} =2.5V, I _D =2.8A		48	58		
Forward Transconductance	g _{FS}	V _{DS} =4.5V, I _D =2.5A		8		S	
Diode Forward Voltage	V _{SD}	I _S =3.4A, V _{GS} =0V		0.8	1.2	V	
Dynamic							
Total Gate Charge	Q _g	V _{DS} =15V, V _{GS} =10V I _D ≅2.6A		3.0	4.5	nC	
Gate-Source Charge	Q _{gs}			1.6			
Gate-Drain Charge	Q _{gd}			0.6			
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V f=1MHz		320		pF	
Output Capacitance	C _{oss}			70			
Reverse Transfer Capacitance	C _{rss}			30			
Turn-On Time	t _{d(on)}	V _{DD} =15V, R _L =15Ω I _D ≅1.0A, V _{GEN} =10V R _G =6Ω		8	12	ns	
	t _r			12	18		
Turn-Off Time	t _{d(off)}				15		30
	t _f				8		15

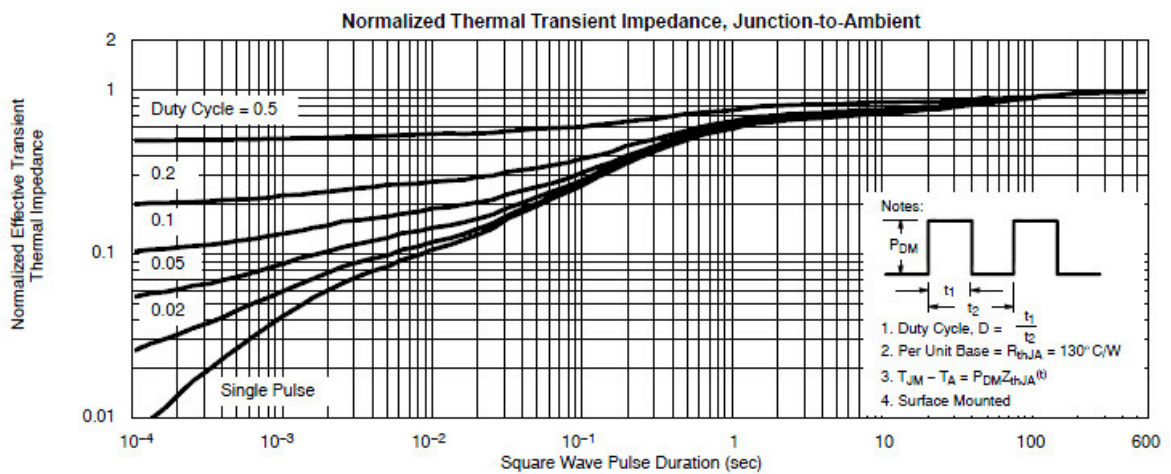
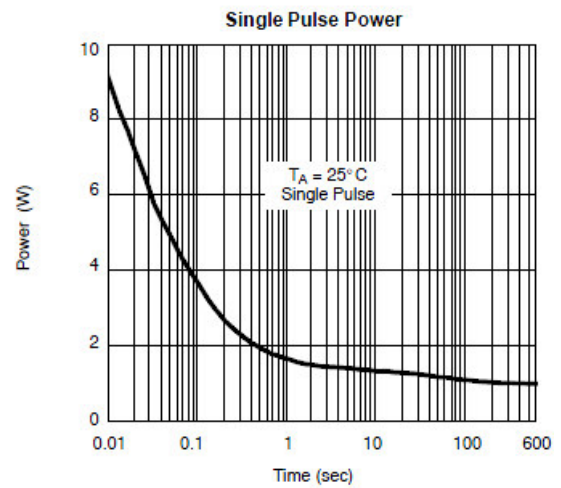
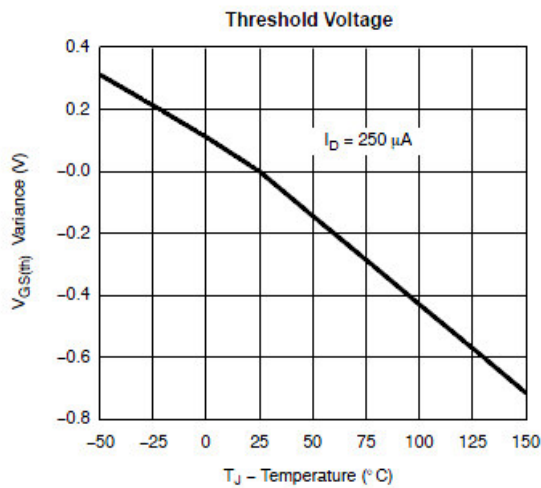
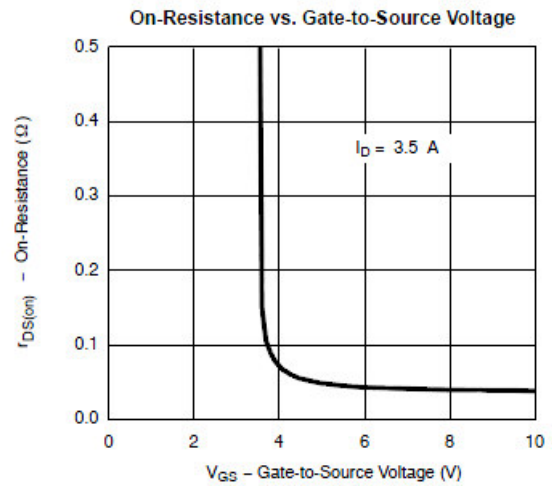
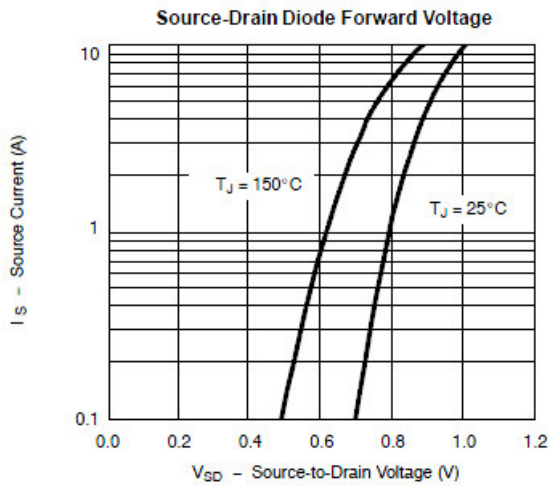


Typical Characteristics





Typical Characteristics



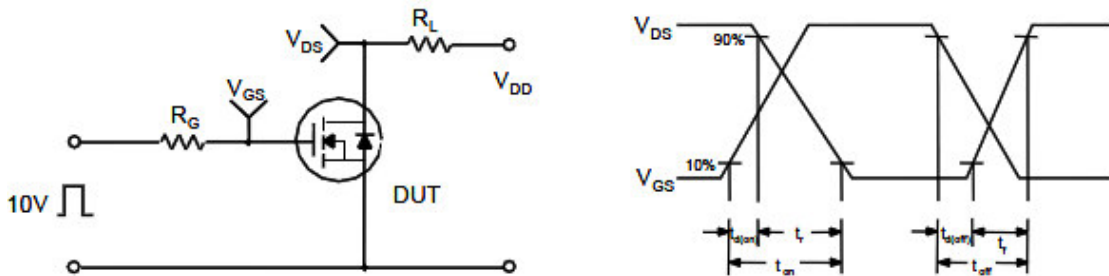


Typical Characteristics

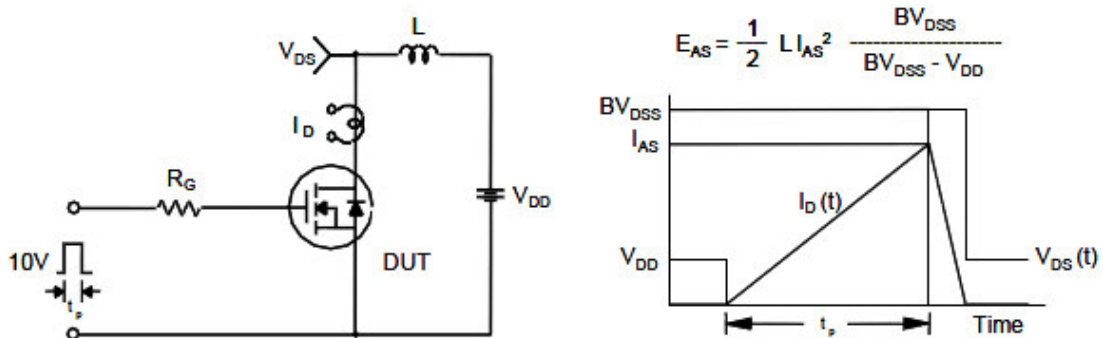
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

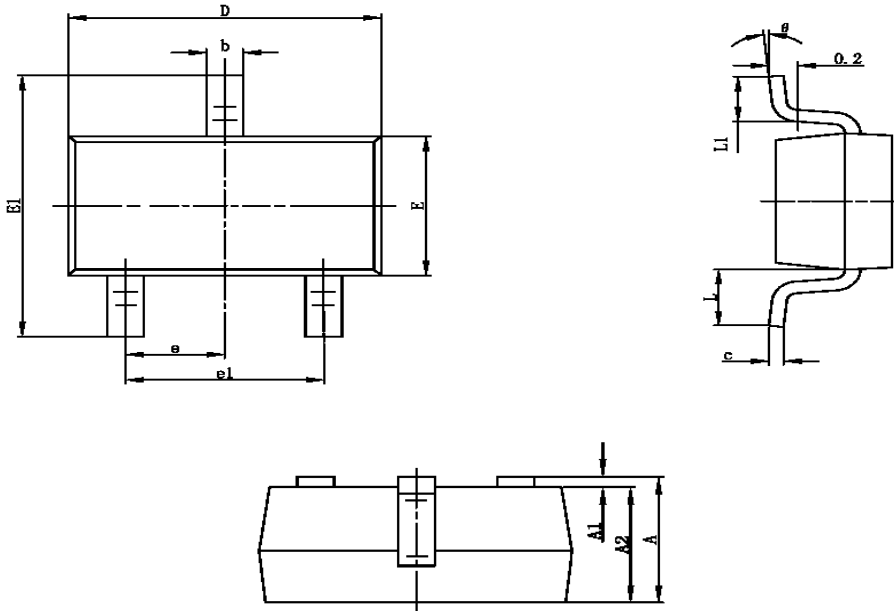


Unclamped Inductive Switching Test Circuit & Waveforms





Package Information (SOT-23-3L)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.400	0.012	0.016
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.700REF		0.028REF	
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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